DSA7504

Silicon PNP epitaxial planar type

For low frequency amplification

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Packaging

DSA7504×0L Embossed type (Thermo-compression sealing): 1000 pcs / reel (standard)

■ Package

- Code

  MiniP3-F2-B

  Package dimension clicks here.→

- Pin Name
  1. Base
  2. Collector
  3. Emitter

■ Marking Symbol: 4F

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	–30	V
Collector-emitter voltage (Base open)	V_{CEO}	–20	V
Emitter-base voltage (Collector open)	V_{EBO}	–7	V
Collector current	I_C	–4	A
Peak collector current	I_{CP}	–7	A
Collector power dissipation *	P_C	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	–55 to +150	°C

Note) *: Printed circuit board: Copper foil area of 1 cm^2 or more, and the board thickness of 1.7 mm for the collector portion
Absolute maximum rating without heat sink for P_C is 0.5 W

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

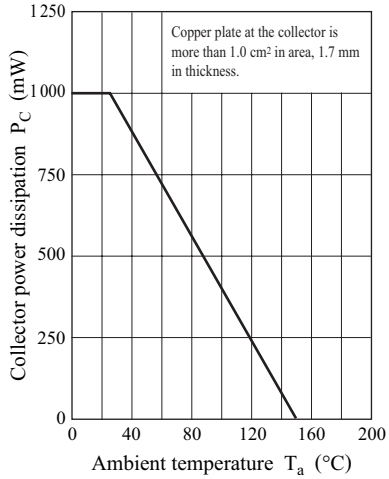
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = –10\ \mu A$, $I_E = 0$	–30			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = –1$ mA, $I_B = 0$	–20			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = –10\ \mu A$, $I_C = 0$	–7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = –30$ V, $I_E = 0$			– 0.1	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = –7$ V, $I_C = 0$			– 0.1	
Forward current transfer ratio *1, 2	h_{FE}	$V_{CE} = –2$ V, $I_C = –2$ A	120		315	—
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = –3$ A, $I_B = – 0.1$ A		– 0.7	–1.0	V
Transition frequency	f_T	$V_{CE} = –6$ V, $I_C = –50$ mA		180		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = –20$ V, $I_E = 0$, f = 1 MHz		30		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. *1: Pulse measurement
*2: Rank classification

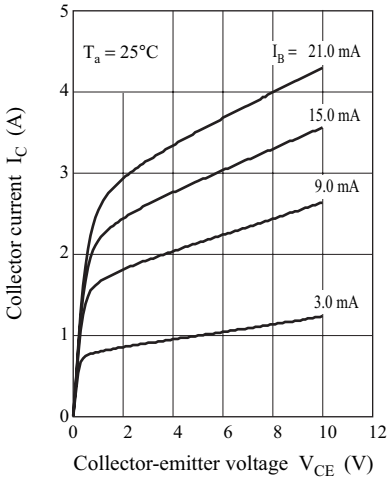
Code	Q	R	0
Rank	Q	R	No-rank
h_{FE}	120 to 205	180 to 315	120 to 315
Marking Symbol	4FQ	4FR	4F

Product of no-rank is not classified and have no marking symbol for rank.

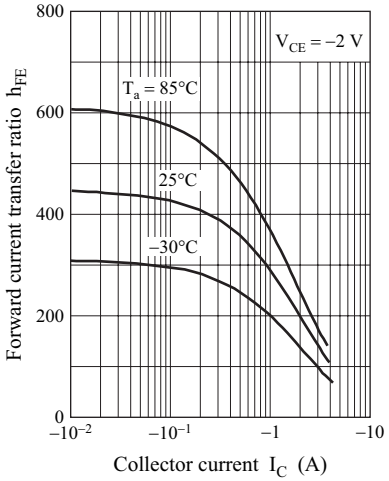
P_C — T_a



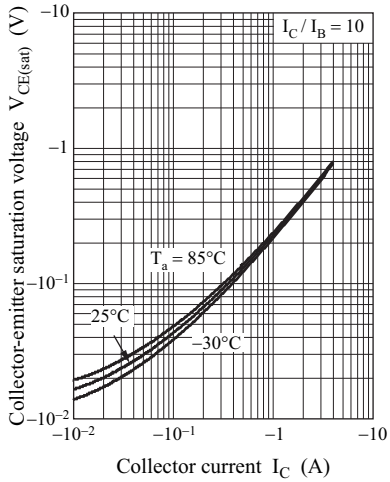
I_C — V_{CE}



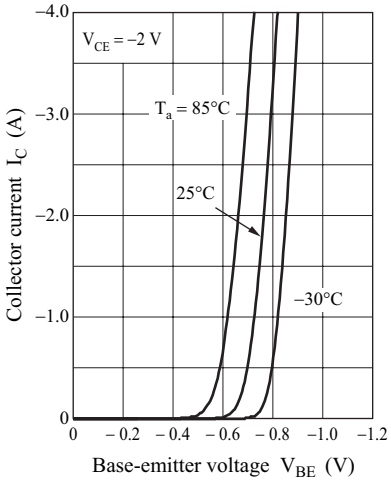
h_{FE} — I_C



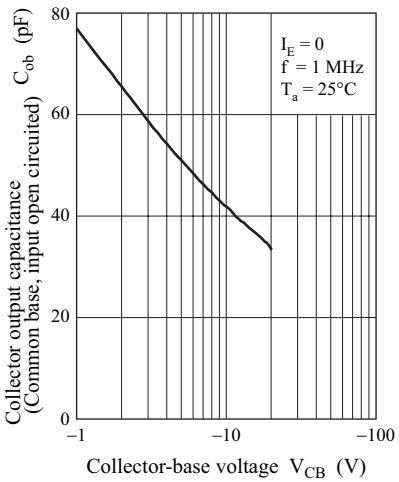
$V_{CE(sat)}$ — I_C



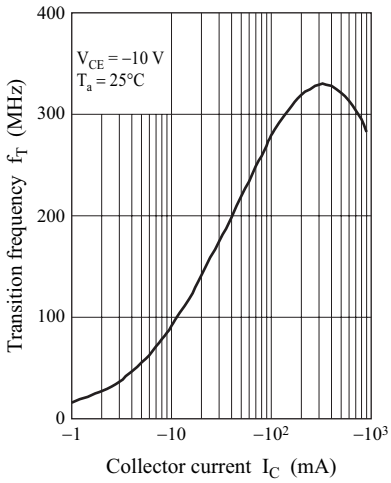
I_C — V_{BE}



C_{ob} — V_{CB}



f_T — I_C



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